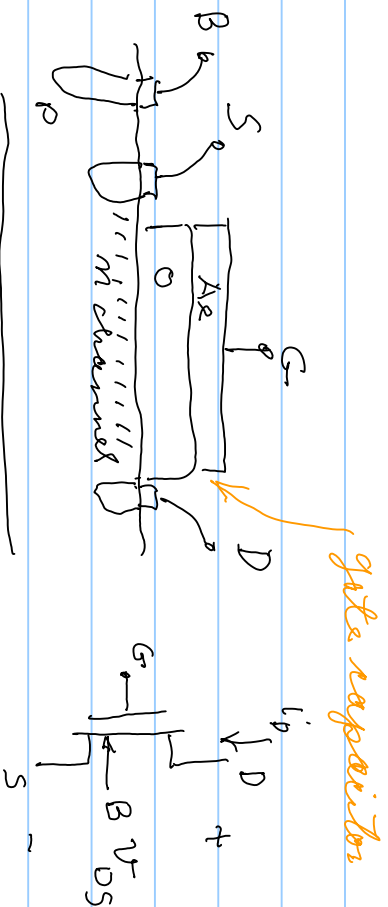


MOS = metal oxide silicon

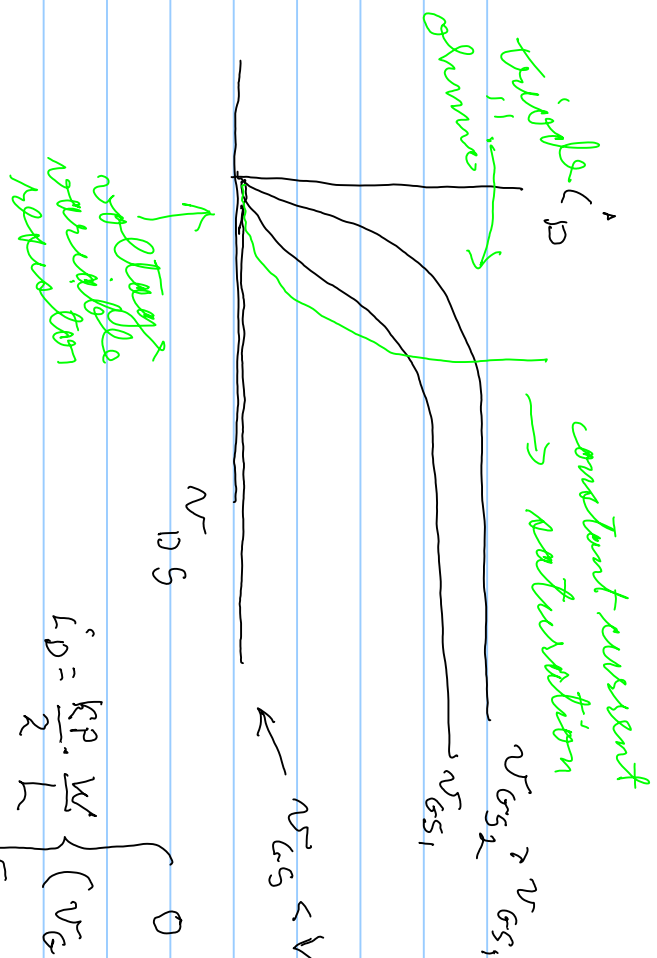
B = bulk

S = source, D = drain

G = gate



NMOS  $V_D > V_G$



$v_{GS} < V_{th} \Rightarrow i_D = 0$   
*cut-off*

$$i_D = f(v_{GS}, v_{DS})$$

$$i_D = \frac{k_p}{2} \cdot \frac{W}{L}$$

$$\begin{cases} 0 & v_{GS} \leq V_{th} & v_{DS} \geq 0 & \text{cut-off} \\ R (v_{GS} - V_{th})^2 (1 + \lambda v_{DS}) & v_{GS} > V_{th} & v_{DS} \geq 0 & \text{sat} \end{cases}$$

$v_{GS} \geq V_{th}$   
 $v_{DS} \geq V_{th}$

$V_{th} = V_{T0}$  if  $v_{BS} = 0$  voltage controlled VCCS if operates in saturation

$$i_D = I_D + \frac{\partial i_D}{\partial v_{GS}} \left( v_{GS} - V_{GS} \right) + \frac{\partial i_D}{\partial v_{DS}} \left( v_{DS} - V_{DS} \right) + \dots$$

DC,  $V_{GS}$ ,  $V_{DS}$  = bias values  
= DC @ Q

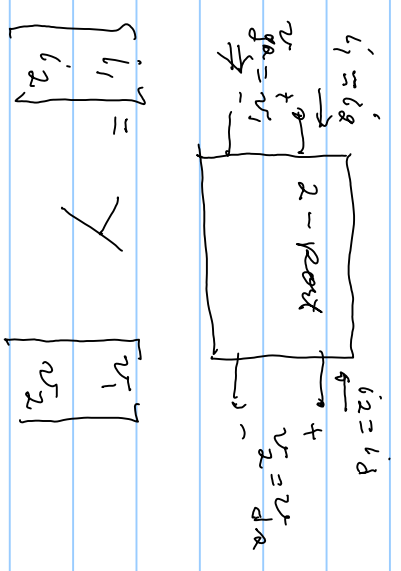
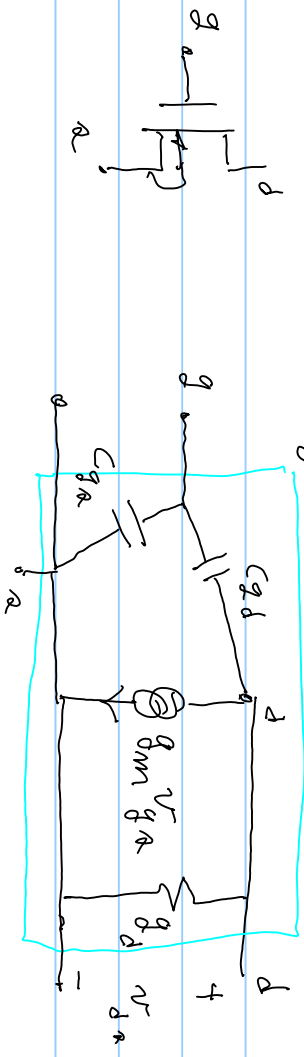
$$v_D = v_D - I_D, \quad v_{gs} = v_{GS} - V_{GS}, \quad v_{ds} = v_{DS} - V_{DS}$$

$$i_D = \frac{\partial i_D}{\partial v_{gs}} v_{gs} + \frac{\partial i_D}{\partial v_{ds}} v_{ds}$$

IG = 0,  $i_g \Rightarrow$  see a capacitor

$$i_g = \alpha C_{gd} v_{gs} + \alpha C_{gd} v_{gs}$$

for B=S



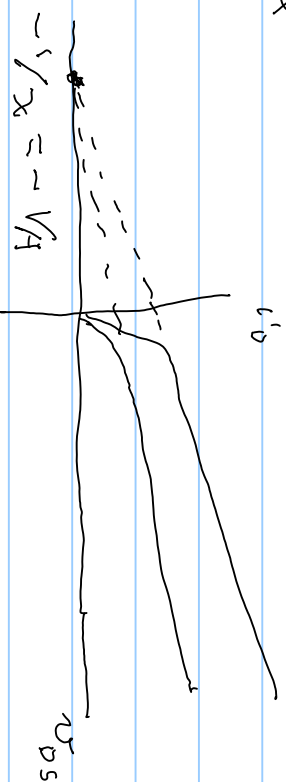
$$g_m = \text{mutual conductance} = \frac{\partial i_D}{\partial v_{GS}} \Big|_Q$$

Q is in saturation region  $i_D = \frac{K_P}{2} W_L (v_{GS} - V_{T0})^2 (1 + \lambda v_{DS})$

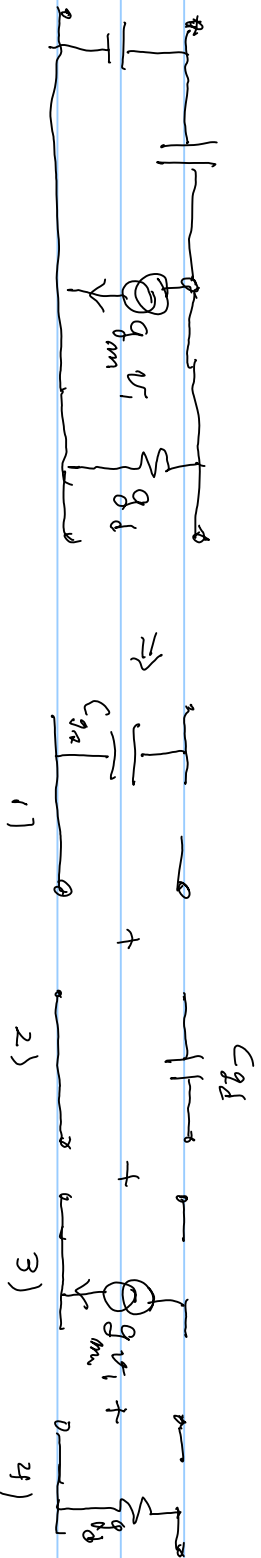
$$\frac{\partial i_D}{\partial v_{GS}} \Big|_Q = 2 \cdot \frac{K_P}{2} (W_L) (v_{GS} - V_{T0}) (1 + \lambda v_{DS}) \Big|_Q = 2 \frac{i_D}{(v_{GS} - V_{T0})} \Big|_Q = 2 \frac{I_D}{(V_{GS} - V_{T0})} = g_m$$

$$\frac{\partial i_D}{\partial v_{DS}} \Big|_Q = \lambda \left[ \frac{K_P}{2} W_L (v_{GS} - V_{T0})^2 \right] \Big|_Q = \lambda \cdot \frac{I_D}{(1 + \lambda v_{DS})} \approx \lambda I_D$$

$$\lambda = 1/V_A, \quad V_A = \text{Early voltage}$$



Other markings



$$Y_1 = \begin{bmatrix} \infty & C_{gs} & 0 \\ 0 & 0 & 0 \end{bmatrix}, \quad Y_2 = \begin{bmatrix} R_L C_{gd} & -R_L C_{gd} \\ -R_L C_{gd} & R_L C_{gd} \end{bmatrix}, \quad Y_3 = \begin{bmatrix} 0 & 0 \\ g_m & 0 \end{bmatrix}, \quad Y_4 = \begin{bmatrix} 0 & 0 \\ 0 & g_d \end{bmatrix}$$

$$Y_3 + Y_4 = \begin{bmatrix} 0 & 0 \\ g_m & g_d \end{bmatrix} \text{ when } R = 0 \Rightarrow \text{very low frequency } X$$